

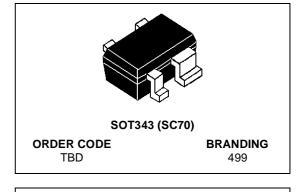
START499 NPN Silicon RF Transistor

PRELIMINARY DATA

- HIGH EFFICIENCY
- HIGH GAIN
- LINEAR AND NON LINEAR OPERATION
- TRANSITION FREQUENCY 42GHz
- ULTRA MINIATURE SOT343 (SC70) PACKAGE

DESCRIPTION

START499 is a product of the START family that provide the market with a Si state-of-art RF process. Manufactured in St 3rd generation bipolar process, it offers the highest power, gain and efficiency in SOT343 for given breakdown voltage (BVceo). Suitable for a wide range of applications up to 5GHz, it shows a performance level achieved before with GaAs products only.



APPLICATIONS

- PA FOR DECT OR PHS
- PA STAGE FOR WIRELESS LAN AND BLUETOOTH @ 2.5GHz
- DRIVER FOR 1W AND MORE PA

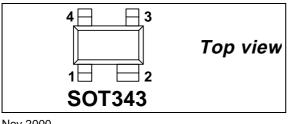
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{ceo}	Collector emitter voltage	4.5	V	
V _{cbo}	Collector base voltage	15	V	
V _{ebo}	Emitter base voltage	1.5	V mA	
I _c	Collector current	250		
I _b	Base current	32	mA	
P _{tot}	Total dissipation at $T_c = 25 \ ^{o}C$	900	mW	
T _{stg}	Storage temperature	-65 to 150	°C	
Тj	Max. operating junction temperature	150	°C	

ABSOLUTE MAXIMUM RATINGS

R _{thjs}	Thermal Resistance Junction soldering point	150	°C/W
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PINOUT



PIN CONNECTION

Pin No.	Description		
1	BASE		
3	COLLECTOR		
2,4	EMITTER		

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Symbol	Parameter	Test Conditions	Test Conditions Min.		Max.	Unit
BV _{ceo}	Collector emitter breackdown voltage	Ic = 1mA, Ib = 0A	4.5	5		V
I _{cbo}	Collector cutoff current	Vcb = 3V, le = 0A			1.2	μΑ
l _{ebo}	Emitter-base cutoff current	Veb = 1.5V, Ic = 0A			120	μΑ
Hfe	DC current gain	lc = 160mA, Vce = 4V	50	90	150	
G	Power gain	Ic =200mA, Vce = 3V, f = 1.8GHz		14.5		dB
P _{-1dB}	1dB compression point	Ic = 200mA,Vce = 3V, f = 1.8GHz		24		dBm
IP3	Ouput third order intercept point	Ic = 200mA,Vce = 3V, f = 1.8GHz		33		dBm

ELECTRICAL CHARACTERISTICS (T_j=25 °C,unless otherwise specified)

QUICK REFERENCE DATA

MODE OF OPERATION	f	V _{CE}	P _L	G _P	ղ Ը	
	(GHz)	(V)	(dBm)	(dB)	(%)	
Class-AB (Icq = 5mA)	1.9	3.6	26	≥11	typ. 63	

COMMON EMITTER S-PARAMETERS (V_{CE} = 2V, I_C = 200mA)

f	S	11	S ₂₁		S ₁₂		\$ ₂₂	
GHz	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.1	0.718	-168.7	53.19	124.7	0.004	70.2	0.654	-103.1
0.5	0.821	175.1	13.59	88.1	0.014	56.4	0.648	-167.9
1	0.834	164.3	6.82	73.4	0.025	59.3	0.625	176.2
1.5	0.838	154.9	4.53	61.3	0.036	57.1	0.664	166.7
1.8	0.844	149.6	3.72	54.6	0.042	53.4	0.671	161.6
2	0.847	146.3	3.29	50.2	0.046	50.2	0.678	158.3
2.5	0.855	138.2	2.54	40.2	0.054	44.6	0.693	150.9
3	0.863	131.9	2.03	31.7	0.060	39.8	0.714	144.5
3.5	0.871	125.4	1.67	22.7	0.066	34.5	0.727	138.8
4	0.873	119.6	1.43	14.6	0.075	29.7	0.741	133.6

K — 1.30 ≻ 1.15-1.35 2.00-2.20 H - 1.15 K К 0.55-0.65 1.90-2.10 1.15-1.35 Ί 0.80-1.00 0.00-0.10 - 0.45 0.25-0.35 -0.10-0.20

PACKAGE DIMENSIONS SOT343 (SC-70 4 leads)

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